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March 2015



FGH40N60SF 600 V, 40 A Field Stop IGBT

Features

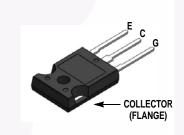
- High Current Capability
- Low Saturation Voltage: V_{CE(sat)} = 2.3 V @ I_C = 40 A
- High Input Impedance
- Fast Switching: $E_{OFF} = 8 \text{ uJ/A}$
- RoHS Compliant

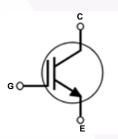
Applications

• Solar Inverter, UPS, Welder, PFC

General Description

Using novel field stop IGBT technology, Fairchild's field stop IGBTs offer the optimum performance for solar inverter, UPS, welder and PFC applications where low conduction and switching losses are essential.





Absolute Maximum Ratings

Symbol	Description		Ratings	Unit	
V _{CES}	Collector to Emitter Voltage	600	V		
V _{GES}	Gate to Emitter Voltage	±20	V		
	Transient Gate-to-Emitter Voltage	±30	V		
I _C	Collector Current	@ T _C = 25°C	80	A	
	Collector Current	@ T _C = 100 ^o C	40	A	
I _{CM (1)}	Pulsed Collector Current	@ T _C = 25°C	120	А	
PD	Maximum Power Dissipation $@T_{C} = 25^{\circ}C$		290	W	
. D	Maximum Power Dissipation $@T_{C} = 100^{\circ}C$		116	W	
Т _Ј	Operating Junction Temperature	-55 to +150	°C		
T _{stg}	Storage Temperature Range	-55 to +150	°C		
TL	Maximum Lead Temp. for soldering Purposes, 1/8" from case for 5 seconds	300	°C		

Notes:

1: Repetitive rating: Pulse width limited by max. junction temperature

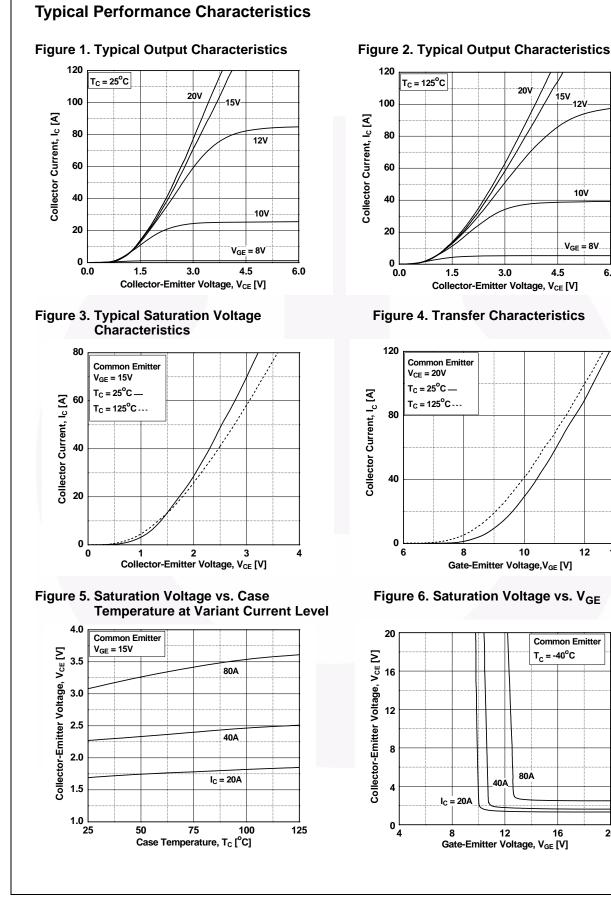
Thermal Characteristics

Symbol	Parameter	Тур.	Max.	Unit	
$R_{\theta JC}$ (IGBT)	Thermal Resistance, Junction to Case	-	0.43	°C/W	
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	-	40	°C/W	

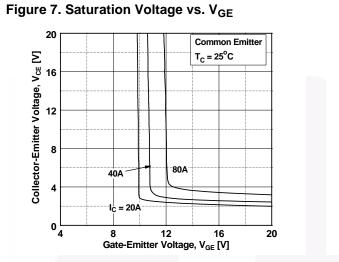
Part Number		Top Mark	Package	Packing Method	Reel Size	Tape Width	Qu	Quantity	
FGH40N60	GH40N60SFTU FGH40N60SF TO-247		Tube	N/A	N/A		30		
Electric	al Ch	aracteristic	s of the l	GBT $T_{C} = 25^{\circ}C$ unless other	rwise noted				
Symbol	ol Parameter			Test Conditio	ns Mir	n. Typ.	Max.	Unit	
Off Charge	toriction				·				
BV _{CES}	Collector to Emitter Breakdown Voltage			V _{GE} = 0 V, I _C = 250 μA	600		_	V	
ΔBV _{CES} /	Collector to Emitter Breakdown Voltage Temperature Coefficient of Breakdown			000			v		
ΔD_{VCES}^{\prime}	Voltage			V_{GE} = 0 V, I_C = 250 μ A	-	0.6	-	V/ºC	
I _{CES}	Collect	or Cut-Off Current		$V_{CE} = V_{CES}, V_{GE} = 0 V$	-	-	250	μA	
I _{GES}	G-E Le	akage Current		$V_{GE} = V_{GES}, V_{CE} = 0 V$	-	-	±400	nA	
On Charac	1						6.5		
V _{GE(th)}	G-E Th	reshold Voltage		$I_{C} = 250 \ \mu A, \ V_{CE} = V_{GE}$	4.0		6.5	V	
V _{CE(sat)}	Collect	or to Emitter Satur	ation Voltage	$I_{C} = 40 \text{ A}, V_{GE} = 15 \text{ V}$ $I_{C} = 40 \text{ A}, V_{GE} = 15 \text{ V},$	-	2.3	2.9	V	
CE(Sat)	Constant of Emiliar Outeration voltage		$T_{C} = 40 \text{ A}, V_{GE} = 15 \text{ V},$ $T_{C} = 125^{\circ}\text{C}$	-	2.5	-	V		
				-					
Dynamic C	haracte	ristics							
C _{ies}	Input C	apacitance		V _{CE} = 30 V, V _{GE} = 0 V, f = 1 MHz	-	2110	-	pF	
C _{oes}	Output	Capacitance			-	200	-	pF	
C _{res}	Revers	Reverse Transfer Capacitance			-	60	-	pF	
Switching	Charact	eristics							
t _{d(on)}	1	n Delay Time			-	25	-	ns	
t _r	Rise Ti	Rise Time Turn-Off Delay Time Fall Time		-	-	42	-	ns	
t _{d(off)}	Turn-O			$V_{\rm CC} = 400 \text{ V}, \text{ I}_{\rm C} = 40 \text{ A},$	-	115	-	ns	
t _f	Fall Tin			$R_{G} = 10 \Omega$, $V_{GE} = 15 V$,	-	27	54	ns	
Eon	Turn-O	n Switching Loss		Inductive Load, T _C = 25 ^o C	°C -	1.13	-	mJ	
E _{off}	Turn-O	ff Switching Loss			-	0.31	-	mJ	
E _{ts}	Total S	witching Loss			-	1.44	-	mJ	
t _{d(on)}	Turn-O	n Delay Time			-	24	-	ns	
t _r	Rise Ti	me		1	-	43	-	ns	
t _{d(off)}	Turn-O	ff Delay Time		$V_{CC} = 400 \text{ V}, \text{ I}_{C} = 40 \text{ A},$ $R_{G} = 10 \Omega, V_{GE} = 15 \text{ V},$	-	120	-	ns	
t _f	Fall Tin	ne				30	-	ns	
E _{on}	Turn-O	n Switching Loss		Inductive Load, T _C = 12	5°C -	1.14	-	mJ	
E _{off}	Turn-O	ff Switching Loss			-	0.48	- (mJ	
E _{ts}	Total S	witching Loss			-	1.62	-	mJ	
Qg	Total G	ate Charge			-	120	-	nC	
Q _{ge}	Gate to	Emitter Charge		$V_{CE} = 400 \text{ V}, I_{C} = 40 \text{ A},$	-	14	-	nC	
Q _{gc}	Gate to	Collector Charge		V _{GE} = 15 V	-	58	_	nC	

6.0

13



20



Typical Performance Characteristics

Figure 9. Capacitance Characteristics

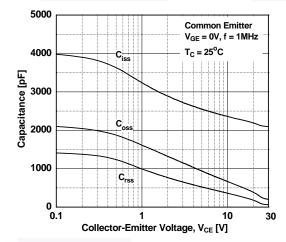


Figure 11. SOA Characteristics

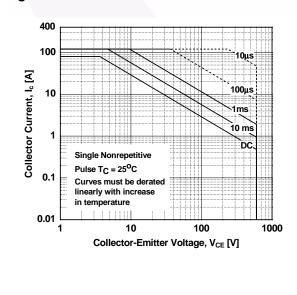


Figure 8. Saturation Voltage vs. V_{GE}

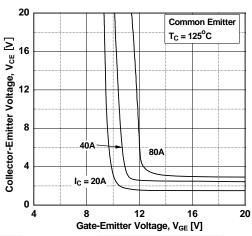


Figure 10. Gate charge Characteristics

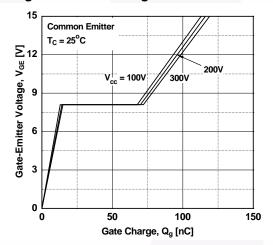
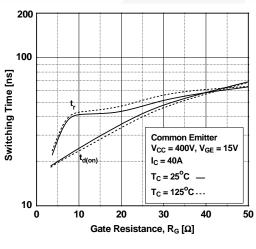
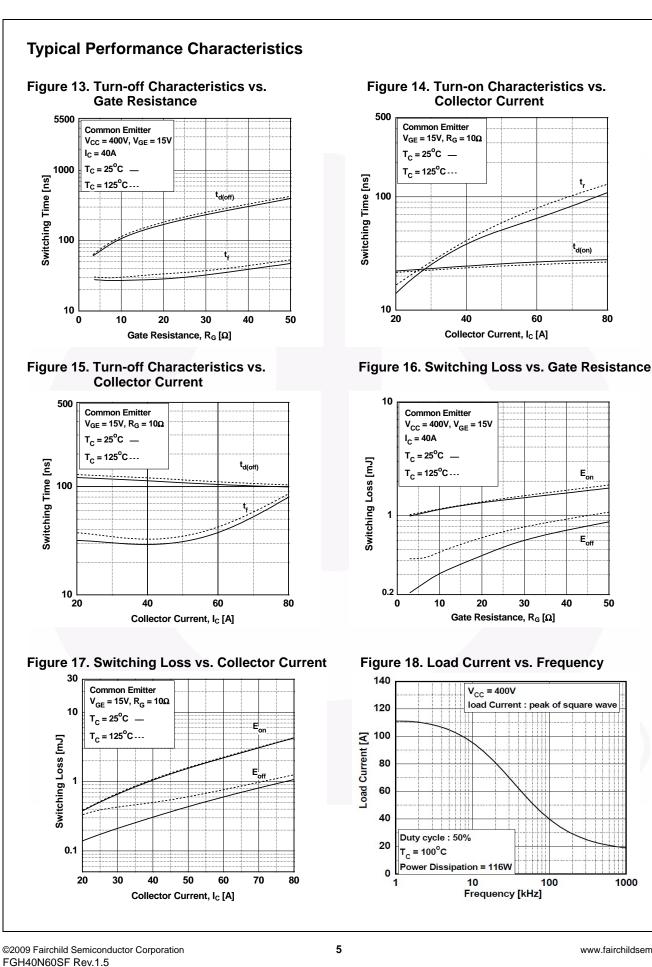


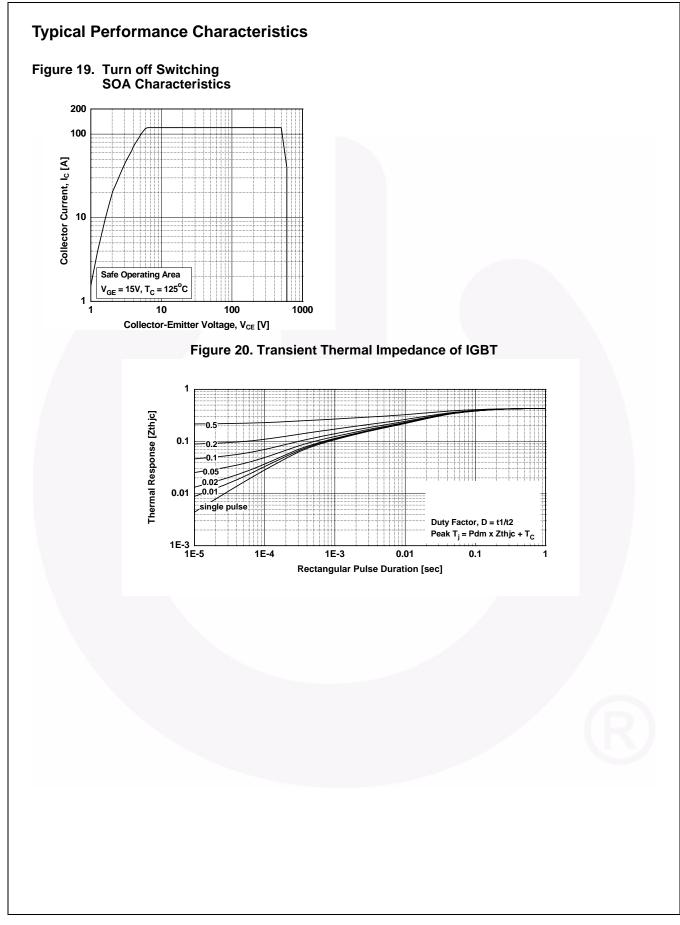
Figure 12. Turn-on Characteristics vs. Gate Resistance

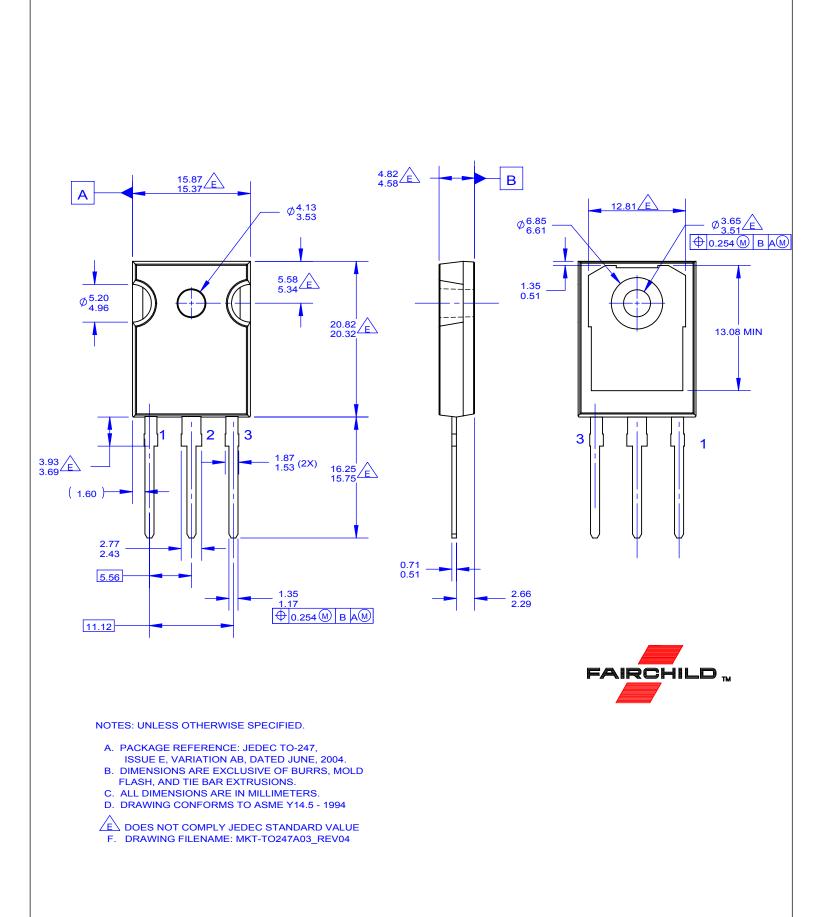


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